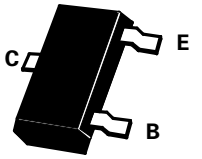
SOT23 PNP SILICON PLANAR MEDIUM POWER TRANSISTOR

ISSUE 4 – MARCH 2001

BCX17

PARTMARKING DETAILS – BCX17 – T1
BCX17R – T4

COMPLIMENTARY TYPES - BCX19



SOT23

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Emitter Voltage	V_{CES}	-50	V
Collector-Emitter Voltage (I_C =-10mA)	V_{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-500	mA
Peak Collector Current	I_{CM}	-1000	mA
Peak Emitter Current	I_{EM}	-1000	mA
Base Current	I_B	-100	mA
Peak Base Current	I_{BM}	-200	mA
Power Dissipation at T_{amb}=25°C	P_{tot}	330	mW
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Cut-Off Current	I_{CBO}			-100 -200	nA µA	I_E =0, V_{CB}=-20V I_E =0, V_{CB}=-20V, T_j=150°C
Emitter-Base Cut-Off Current	I_{EBO}			-10	µA	I_C =0, V_{EB}=-1V
Base-Emitter Voltage	V_{BE}			-1.2	V	I_C =-500mA, V_{CE} =-1V*
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-620	mV	I_C =-500mA, I_B =-50mA*
Static Forward Current Transfer Ratio	h_{FE}	100 70 40		600		I_C =-100mA, V_{CE} =-1V I_C =-300mA, V_{CE} =-1V* I_C =-500mA, V_{CE} =-1V*
Transition Frequency	f_T		100		MHz	I_C =-10mA, V_{CE} =-5V f =35MHz
Output Capacitance	C_{obo}		8.0		pF	V_{CB} =-10V, f =1MHz

*Measured under pulsed conditions.
Spice parameter data is available upon request for this device

ZETEX